Cascadable Broadband InGaP MMIC Amplifier
DC-14 GHz P1A-1500GN

Description

P1dB's P1A-1500GN cascadable broadband InGaP HBT MMIC amplifier is a low-cost high-performance solution for your general-purpose RF and microwave amplification needs. This 50-ohm gain block is based upon a mature and reliable HBT (Heterojunction Bipolar Transistor) process and utilizes proprietary MMIC design techniques, providing best in class performance for small-signal applications.

The P1A-1500GN is packaged in a low-cost surface-mount ceramic package shipped in tape and reel, enabling ease of assembly for high-volume applications. The P1A-1500GN has a very simple application circuit including external DC decoupling caps which limit the low-frequency response as well as an external dropping resistor that provides excellent performance stability and design flexibility.

The P1A-1500GN is available in either packaged or die form. Packaged parts are available in bulk or tape and reel. Connectorized evaluation board designs are also available for characterization purposes.

Features

- Reliable Low-Cost InGaP HBT Design
- Extremely Broadband (optimized for low parasitic reactances)
- Excellent Gain Flatness and High P1dB
- Single Power Supply Operation
- 50 Ω Input/Output Matched
- Ceramic Micro X Package

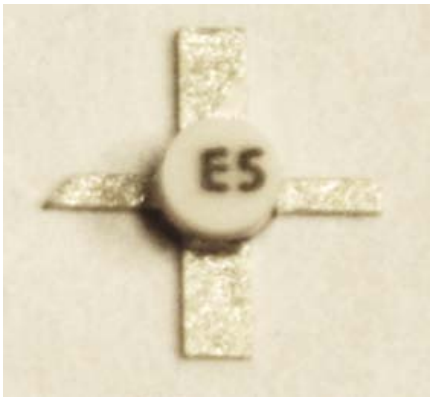
Applications

- Narrowband and Broadband Applications for both Commercial and Military Designs
- Linear & saturated amplifier applications.
- Gain stage or driver amplifiers utilized in many applications such as point to point radio, test equipment, VSAT, and military communication systems.

Ordering Information

Part Number	Description
P1A-1500GN	Individual Part
P1A-1500GND	Individual Die
P1A-1500GNK1	Tape & Reel, 1000 Pieces
P1A-1500GNE	Evaluation Board

Package Information



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Absolute Maximum Ratings

Parameter	Rating	Units
RF Input Power	+20	dBm
Power Dissipation	308	mW
Device Current	74	mA
Channel Temperture	150	°C
Operating Temperature	-45 to +85	°C
Storage Temperature	-65 to +150	°C
ESD Level (HBM)	Class 1A	
Moisture Sensitivity Level	MSL-2	

Caution! ESD sensitive device.
Caution! Exceeding any one or a combination of these limits may cause permanent damage.
RoHS Compliant

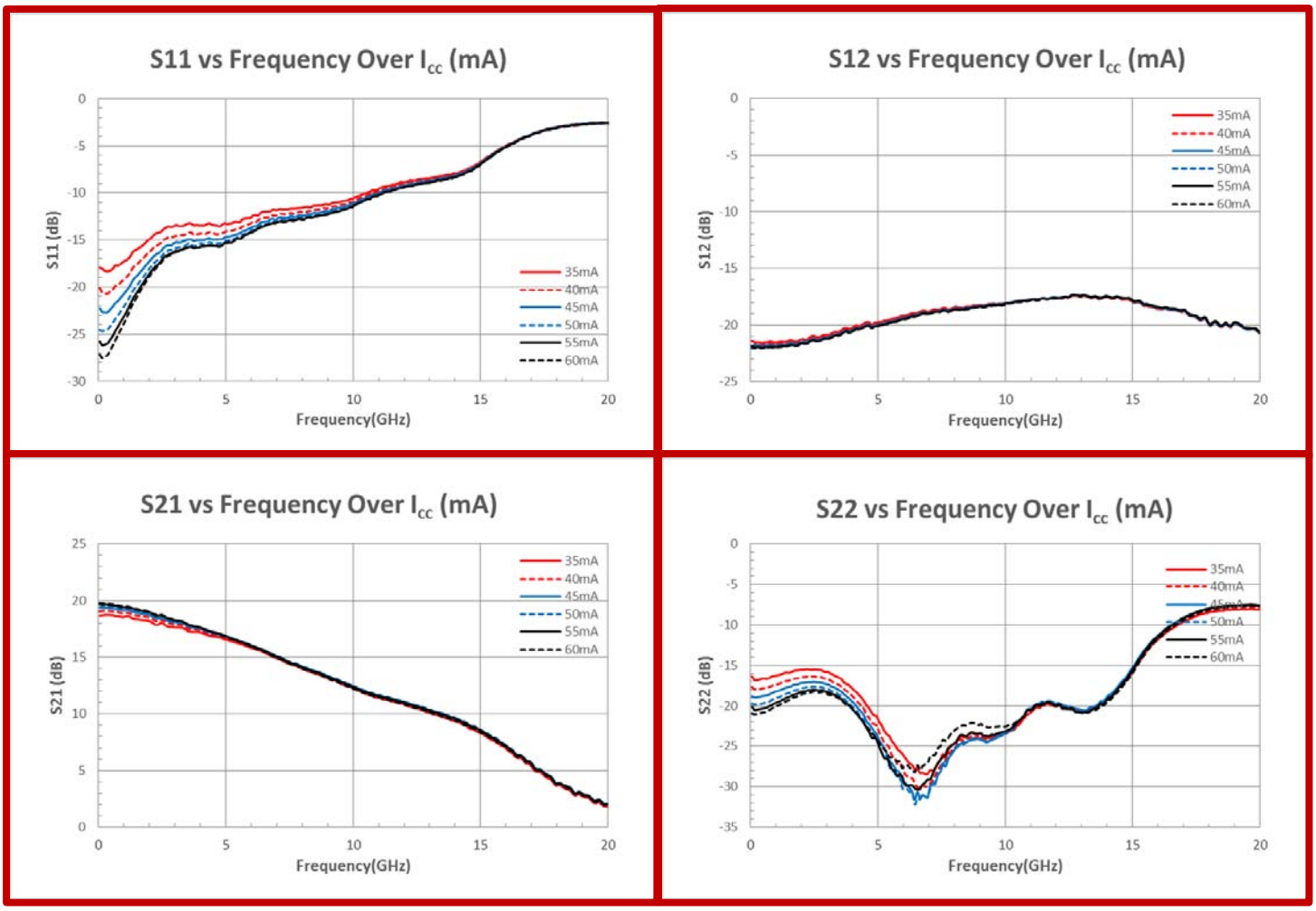
Nominal Operating Parameters

Parameter	Test Conditions	Units	Min.	Typ.	Max.
General Performance		Vd = +4.2V, Icc=50mA, Z_0=50Ω, Ta=+25°C			
Small Signal Power Gain, S_{21}	f=0.1 to 1.0 GHz f=1.0 to 4.0 GHz f=4.0 to 6.0 GHz f=6.0 to 12.0 GHz f=12.0 to 14.0 GHz	dB dB dB dB dB	19.2 17.4 15.9 10.9 9.5	19.5 18.4 16.5 13.5 10.5	
Gain Flatness, G_F	f=0.1 to 6.0 GHz	dB		±1.8	
Input and Output VSWR	f=0.1 to 4.0 GHz f=4.0 to 6.0 GHz f=6.0 to 12.0 GHz			2.0:1 2.4:1 2.5:1	
Bandwidth, BW	BW3 (3dB)	GHz		5.5	
Output Power @ 1-dB Compression, P1dB	f =2.0 GHz f =6.0 GHz f=12.0 GHz	dBm dBm dBm		16.3 16.4 13.7	
Noise Figure, NF	f=3.0 GHz	dB		5.5	
3rd Order Intercept, IP3	f=2.0 GHz	dBm		+28	
Reverse Isolation,S_{12}	f=0.1 to 14.0 GHz	dB		-17	
Device Voltage, Vd		V	4.1	4.2	4.3
Gain Temperature Coefficient, $\partial G_T/\partial T$		dB/°C		-0.0015	

Nominal Operating Parameters

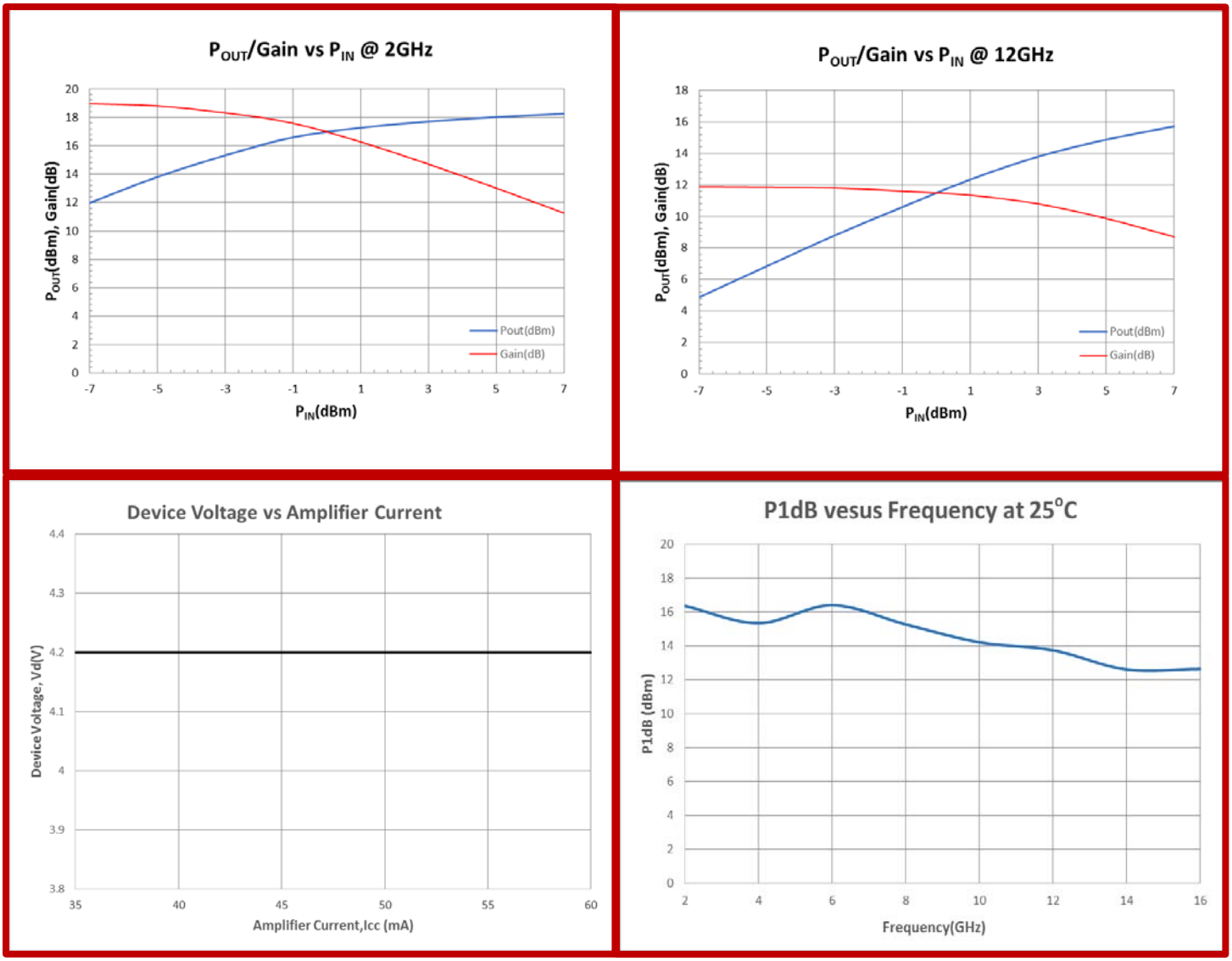
Parameter	Condition	Units	Min.	Typ.	Max.
MTTF versus Temperature at Icc = 50mA					
Case Temperature		°C		85	
Junction Temperature		°C		107	
MTTF		hours		>10^6	
Termal Resistance					
θ_{JC}	$\theta_{JC} = (J_T - T_{CASE})/(V_D * I_{CC})$	°C/W		212	

Typical Performance

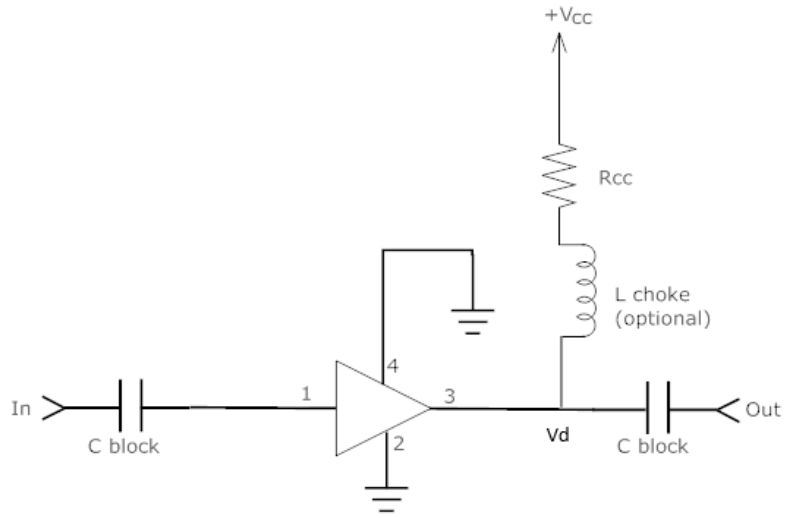


Note: The s-parameter gain results shown above were obtained using a production test fixture.

Typical Performance (continued)

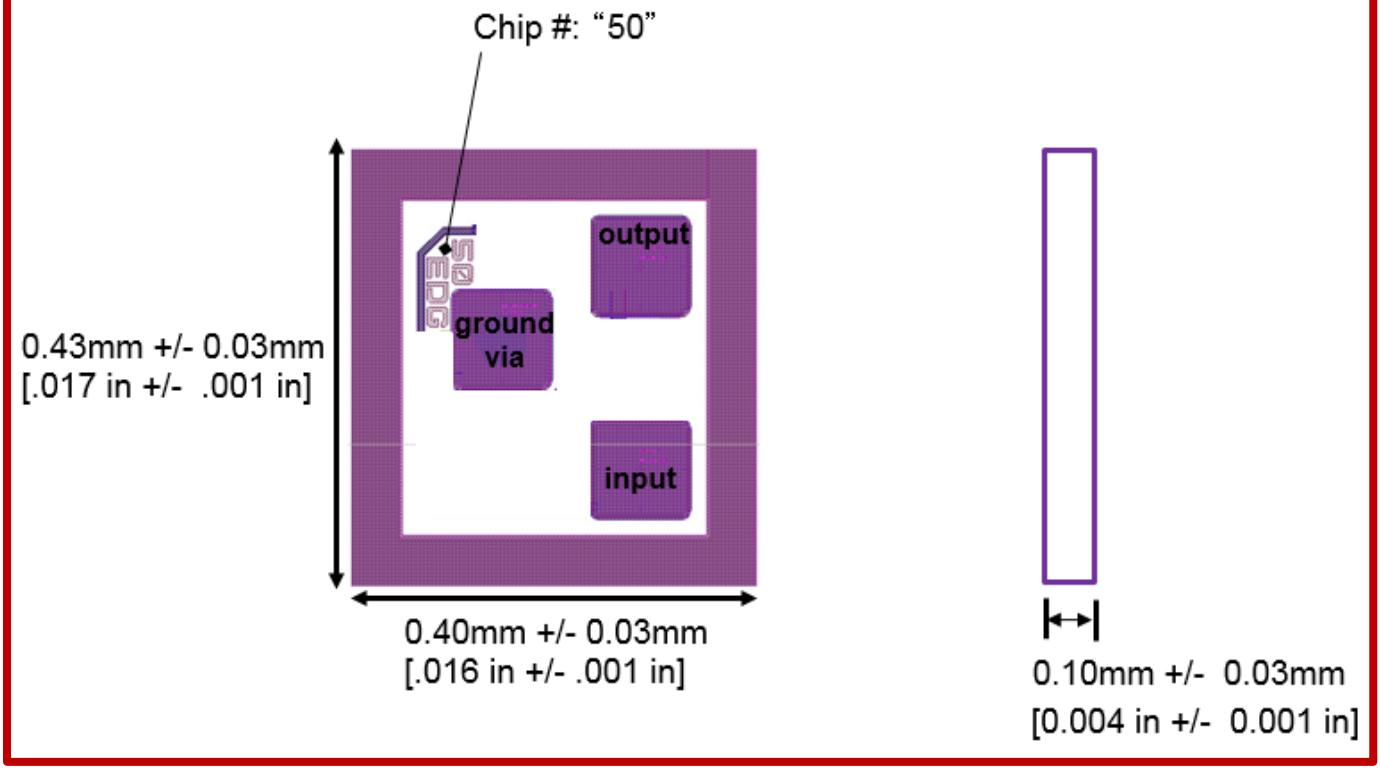


Typical Bias Configuration

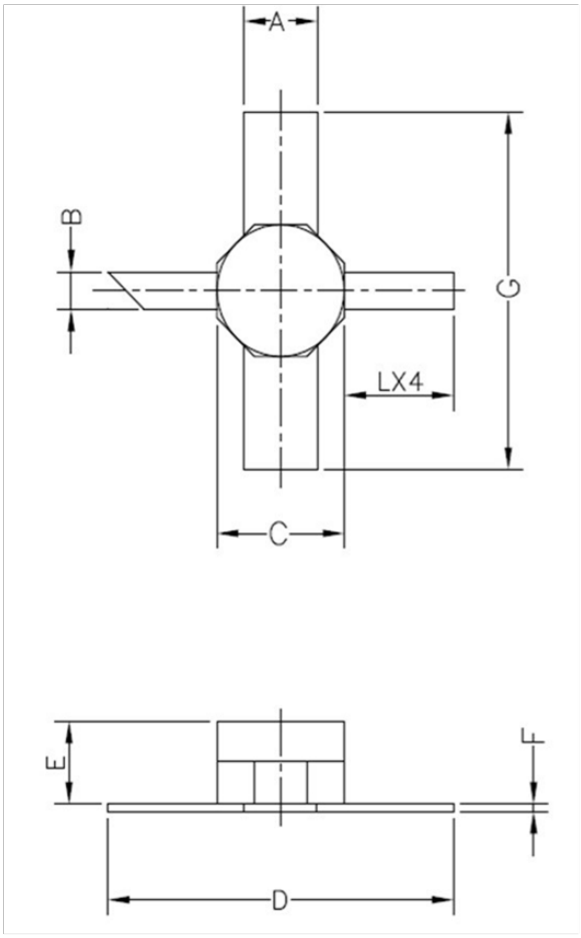


Recommended Bias Resistor Values @ Icc = 50 mA						
Supply Volatage, V_{cc} (V)	5	8	10	12	15	20
Bias Resistor, Rcc (Ω)	16	76	116	156	216	316

Die Drawing



Package Dimensions & Pin Descriptions



Symbol	Milimeters			Inches		
	MIN.	NOM.	MAX.	MIN.	MIN.	MAX.
A	0.92	1.02	1.12	.036	.040	.044
B	0.40	0.50	0.60	.016	.020	.024
C	1.73	1.78	1.83	.068	.070	.072
D	4.73	4.83	4.93	.186	.190	.194
E	1.22MAX.			.048 MAX.		
F	0.071	0.100	0.152	.0028	.0040	.0060
G	4.73	4.83	4.93	.186	.190	.194
L	1.42	1.52	1.62	.056	.060	.064

Pin	Name	Description
1	RF_{in}	RF input pin. A DC blocking capacitor specified for the frequency of operation should be used.
2	Gnd	Ground Connection.
3	RF_{out}	RF output and bias pin. Biasing is accomplished with an external series resistor and a choke inductor. The resistor value is determined by the following equation: $R = \frac{(Vcc - Vd)}{Icc}$
4	Gnd	Ground Connection.